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Substitute for form 1449A/PTO				<i>Complete if Known</i>	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT				Application Number	10/622 353
				Filing Date	
				First Named Inventor	Erwin J. Prinz
				Group Art Unit	
				Examiner Name	
(use as many sheets as necessary)		Sheet		Attorney Docket Number	SC12852TP
1		of	2		

U. S. PATENT DOCUMENTS

FOREIGN PATENT DOCUMENTS

Examiner Signature	TAN T. NGUYEN	Date Considered	10/12/04
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EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation, if not in conformance and not considered. Include copy of this form with next communication to applicant.

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Sheet	2	of	2
		Attorney Docket Number	SC12852TP

OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS				
Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.		T ²
TNT	AC	FUJIWARA, I. et al.; "High speed program/erase sub 100 nm MONOS memory cell"; Advanced Devices R&D Laboratories, LSI, SNC, Sony Corporation; pages 75-77		
TNT	AD	CHAN, T.Y. et al.; "A True Single-Transistor Oxide-Nitride-Oxide EEPROM Device"; IEEE Electron Device Letters; March, 1987; pages 93-95; Vol. EDL-8; No. 3		
TNT	AE	Specification; US Patent Application 10/280,294; Craig T. Swift et al.; Filed 10-25-2002		

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